

Structural Changes in the Solid Solution $(\text{Ti}_{1-x}\text{V}_x)_2\text{O}_3$ as x Varies from Zero to One

CATHERINE E. RICE AND WILLIAM R. ROBINSON*

Department of Chemistry, Purdue University, West Lafayette, Indiana 47907

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The crystal structures of $(\text{Ti}_{1-x}\text{V}_x)_2\text{O}_3$, $x = 0.005, 0.01, 0.02, 0.04, 0.07, 0.30, 0.50, 0.70,$ and 0.90 , have been determined from X-ray diffraction data collected from single crystals. The compounds are rhombohedral, space group $R\bar{3}c$, and are isomorphous with α -alumina. The hexagonal cell dimensions range from $a = 5.1549(6) \text{ \AA}$, $c = 13.627(2) \text{ \AA}$, for $(\text{Ti}_{0.995}\text{V}_{0.005})_2\text{O}_3$ to $a = 4.9813(2) \text{ \AA}$, $c = 13.996(1) \text{ \AA}$ for $(\text{Ti}_{0.10}\text{V}_{0.90})_2\text{O}_3$. The most pronounced effects of V^{3+} substitution occur in the 0 to 7 at % V range and can be described as an increase in the metal–metal distance along the c axis from $2.578(2) \text{ \AA}$ in pure Ti_2O_3 to $2.652(1) \text{ \AA}$ in $(\text{Ti}_{0.93}\text{V}_{0.07})_2\text{O}_3$ coupled with reorganization of the structure in order to maintain constant metal–oxygen distances. These structural changes have been related to both the change from semiconducting to metallic behavior and the disappearance of the 150–350°C resistivity drop which occur with increasing vanadium content in $(\text{Ti}_{1-x}\text{V}_x)_2\text{O}_3$ as x increases from 0.0 to about 0.07. They are consistent with the band theory proposed by others for this system. Indications of unusual structural behavior in the 90–100 at % V range are also noted.

Introduction

The addition of small amounts of V_2O_3 to Ti_2O_3 produces a gradual semiconductor–metal transition (1) much like the one observed in pure Ti_2O_3 upon heating through the 150–350°C region (2, 3). Both electrical transitions are accompanied by similar distortions of the crystal lattice (4, 5), and no change in space group occurs in either case. These transitions have been studied extensively by resistivity and thermoelectric measurements (6, 7), specific heat measurements (8), Raman spectroscopy (9, 10), and ultrasonic attenuation (11, 12). In both cases the structural and electrical changes can be explained in terms of changes in metal–metal bond order which accompany the closing of a small gap between filled and empty d bands in the band structure of the semiconducting phase (1, 13, 14).

In addition to showing a semiconductor–metal transition, low-vanadium alloys in the

* Author to whom correspondence should be addressed.

$(\text{Ti}_{1-x}\text{V}_x)_2\text{O}_3$ system exhibit quite anomalous low-temperature specific heat (15), magnetic susceptibility (16, 17), and magnetoresistance behavior (18). These phenomena have variously been interpreted as indicative of spin glass properties (17), a pseudo-one-dimensional density of states distribution (15), correlative effects leading to heavy polaron formation (19), or the existence of a narrow impurity band near the Fermi level (20). The role of vanadium in this system is still not well understood.

The unit cell parameters in the $(\text{Ti}_{1-x}\text{V}_x)_2\text{O}_3$ system (5, 21) show drastic deviations from Vegard's Law, suggesting complexity in the intimate structural behavior. In the range 0–10% vanadium, the change in cell parameters is analogous to that observed upon heating Ti_2O_3 through its semiconductor–metal transition suggesting that the changes in $(\text{Ti}_{1-x}\text{V}_x)_2\text{O}_3$ might be analogous to those observed (22, 23) in Ti_2O_3 . In addition to the series of high temperature crystal structures of Ti_2O_3 , the room temperature crystal structures of Ti_2O_3 , $(\text{Ti}_{0.9}\text{V}_{0.1})_2\text{O}_3$, and V_2O_3

have been determined (22–27). However, detailed crystal structure information for intermediate concentrations has not been available. In light of the unusual structural, electrical, and magnetic behavior observed in this system, we thought it interesting to study the changes in atomic positions which occur as a function of x in $(\text{Ti}_{1-x}\text{V}_x)_2\text{O}_3$, giving special attention to the low-vanadium regime. Therefore, we have determined the crystal structures of nine such solid solutions where x varies from 0.005 to 0.90.

Experimental

Samples of $(\text{Ti}_{1-x}\text{V}_x)_2\text{O}_3$ ($x = 0.005, 0.01, 0.02, 0.04, 0.07, \text{ and } 0.10$) from single-crystal boules were provided by Professor Honig of this department. The compositions of samples with $x \leq 0.10$ were determined by elemental analysis (1, 15). The other samples were prepared by the Purdue Crystal Growth Facility by melting together the requisite amount of Ti_2O_3 and V_2O_3 in a tri-arc furnace. Past experience in this facility has shown that this technique gives Ti/V ratios within 1% of the nominal composition. Spheres with radii ranging from 0.0060 to 0.0114 cm were ground from fragments of the boules. Weissenberg photographs of representative crystals confirmed the known space group $R\bar{3}c$ (no. 167) and diffractometer measurements for all crystals were compatible with this assignment. No evidence for ordering of vanadium was found.

All crystals were mounted along nonprincipal axes to reduce the effects of multiple diffraction (28). Unit cell parameters and intensities were measured using an Enraf-Nonius CAD-4 diffractometer with graphite monochromated $\text{MoK}\alpha$ radiation. Only unit cell parameters were determined for $x = 0.10$. An incident beam collimator 0.8 mm in diameter at a takeoff angle of 4.0° was used with a receiving aperture located 173 mm from the crystal. The pulse height analyzer used with the scintillation counter was set to admit approximately 95% of the diffraction intensity. Following centering of the crystal, a set of 15 reflections widely separated in reciprocal space was centered and used to determine the

orientation matrix for use in intensity data collection.

Precise unit cell parameters were determined by centering the $K\alpha_1$ ($\lambda = 0.70926 \text{ \AA}$) peak for 50 to 60 reflections, $80^\circ < 2\theta < 100^\circ$, at both positive and negative 2θ and taking the average as the diffraction angle. Hexagonal cell parameters and ESDs (Table I) were calculated by least-squares refinement of the observed 2θ values using the program LCR-2 (29). Unit cell determinations were repeated with different crystals for several samples. In the worst case, the cell dimensions were reproducible within 8 ESDs (4 ESDs from the mean) based on the least-squares fit to the experimental data. Although the cell parameters might be susceptible to the effects of possible systematic error in the diffractometer, the differences between parameters are not.

All reflections in a hemisphere of reciprocal space with $6^\circ < 2\theta < 66^\circ$ were collected for all samples. The θ - 2θ scanning technique with a variable scanning speed was used with a 2θ range of $1.0 + 0.2 \tan \theta$ degrees centered about the average peak position. The aperture was set at $3.0 + 2.11 \tan \theta$ mm wide by 6 mm high. Each reflection was first scanned at a rate of $20.1^\circ \text{ min}^{-1}$ to determine its approximate intensity. Reflections were then scanned twice at a slower rate necessary to accumulate the minimum net count of 1000 counts above background. If the results of the two slow scans were statistically different, they were repeated until agreement was reached. The maximum rate for this slower scan was $20.1^\circ \text{ min}^{-1}$. Those reflections which were too weak to give the desired net count were scanned twice at $1.3^\circ \text{ min}^{-1}$. The intensities of 85% of the reflections were well above the minimum count required, although the counting rates were such that no coincidence corrections were necessary. Background counts were made for $\frac{1}{4}$ of the scan time at each end of both scans. Several standard reflections were monitored every 2 hr and did not show significant intensity changes during the course of the data collection period.

Integrated intensities, I , were obtained using the expression $I = C - 2B$, where C is the sum of the counts collected during the

TABLE I
CRYSTALLOGRAPHIC DATA FOR $(\text{Ti}_{1-x}\text{V}_x)_2\text{O}_3$ WITH STANDARD DEVIATIONS IN PARENTHESES

Parameter	$x=0^a$	0.005	0.01	0.02	0.04	0.07	0.10	0.30	0.50	0.70	0.90	1.00 ^b
a_{hex} (Å)	5.1580(4)	5.1549(6)	5.1493(4)	5.1417(2)	5.1255(6)	5.1090(2)	5.1025(1)	5.0539(3)	5.0174(1)	4.9968(1)	4.9813(2)	4.9492(2)
c_{hex} (Å)	13.611(1)	13.627(2)	13.654(2)	13.686(1)	13.734(4)	13.812(1)	13.829(1)	13.953(2)	13.993(2)	13.996(1)	13.996(1)	13.998(1)
vol (Å ³)	313.6	313.6	313.5	313.3	312.5	312.2	311.8	308.6	305.1	302.6	300.8	296.9
c/a	2.64	2.64	2.65	2.66	2.68	2.70	2.71	2.76	2.79	2.80	2.81	2.83
M_z	0.34485(5)	0.34484(5)	0.34503(5)	0.34519(4)	0.34563(3)	0.34602(4)	0.34614(3) ^c	0.34668(3)	0.34675(4)	0.34682(4)	0.34691(4)	0.34634(4)
β_{11}^d	65(6)	32(4)	27(4)	28(3)	32(3)	41(4)	31(4) ^e	52(3)	41(4)	57(3)	56(3)	57(6)
β_{33}^d	5.4(6)	4.3(5)	2.5(6)	3.8(4)	5.3(4)	4.0(5)	2.3(5) ^e	3.0(4)	3.7(5)	4.5(4)	4.4(4)	1.9(7)
Ox x	0.3133(4)	0.3130(3)	0.3130(4)	0.3126(3)	0.3122(3)	0.3120(4)	0.3114(3) ^e	0.3109(3)	0.3111(4)	0.3114(4)	0.3110(4)	0.3122(5)
β_1^d	76(10)	35(6)	28(7)	27(6)	38(5)	43(7)	36(7) ^e	49(6)	33(7)	50(6)	55(7)	49(10)
β_2^d	87(12)	45(9)	38(10)	37(9)	41(7)	43(9)	36(9) ^e	55(8)	52(10)	58(9)	58(10)	76(14)
β_3^d	6.6(12)	4.0(10)	3.5(11)	4.2(9)	5.6(6)	5.0(8)	2.8(10) ^e	4.5(7)	4.7(8)	5.4(8)	5.7(7)	5.0(10)
β_{13}^e	1.9(13)	1.2(10)	2.2(11)	1.5(11)	2.9(9)	3.1(10)	0.6(10) ^e	2.2(10)	3.9(11)	3.8(11)	4.1(11)	4(2)
R	0.027	0.021	0.024	0.020	0.021	0.019	0.027 ^c	0.027	0.022	0.018	0.017	0.039
R_{wt}	0.030	0.024	0.032	0.027	0.024	0.029	0.030 ^c	0.030	0.028	0.025	0.025	0.048
n	125	126	126	126	126	125	145 ^c	122	121	121	120	98
s^e												
B_M												
B_{0x}												
S												

^a Ref. (23).
^b Ref. (26).
^c Ref. (25).
^d Times 10⁴. For M , $\beta_{11} = \beta_{22}$, $\beta_{13} = \frac{1}{2}\beta_{11}$, and $\beta_{23} = \beta_{13} = 0$. For Ox, $\beta_{12} = \frac{1}{2}\beta_{22}$ and $\beta_{23} = 2\beta_{13}$. The form of the anisotropic temperature factor T is $T = \exp(-\sum_i \sum_j h_i h_j \beta_{ij})$.
^e Times 10⁵.

two slower scans, and B is the sum of the background counts during these scans. A standard deviation was assigned to each measured intensity using the expression $\sigma(I) = [C + 4B]^{1/2}$. The data were corrected for Lorentz polarization effects. The crystals were measured using a microscope with a micrometer eyepiece, and a spherical absorption correction was applied (μR for the crystals ranged from 0.48 to 0.91). Averaging of equivalent reflections gave 120 to 126 symmetry-independent reflections for each crystal. Reflections with $I < \sigma$ were set equal to $\frac{1}{2}\sigma$ and included in the refinement; there were five or six reflections in this category for each data set.

Refinement with both isotropic and anisotropic temperature factors was carried out for each set of intensity data using the RFINE2 program written by Finger (30). The initial atomic parameters in the space group $R\bar{3}c$ were those for Ti_2O_3 (22). The program minimized $\sum w(F_o - F_c)^2$ using the scattering factors for Ti^{3+} , V^{3+} , and O° (31) corrected for real and imaginary anomalous dispersion (32), weights based on average standard deviations ($w = 1/\sigma^2(F) = 4F_o^2/\sigma^2(F^2)$), and an extinction correction of the form $F_{corr} = F_o(1 + sI_o)$. No reflections were rejected from the refinements. Final R values varied from 0.024 to 0.032. Values of the standard deviation of an observation of unit weight are listed in Table I as S . The final atom parameters listed in these tables were used with the variance-covariance matrices to calculate the interatomic distances and bond angles and their ESDs listed in Table II. Distances and angles for $(Ti_{0.9}V_{0.1})_2O_3$ were calculated from the cell parameters of this work and the atom parameters of Ref. (25). Structure factor amplitudes are reported in Table III.

Results

All of the Ti_2O_3 - V_2O_3 alloys studied were found to be isomorphous with α - Al_2O_3 . The structures consist of an approximate hexagonally closest packed array of oxide ions with metal ions occupying two-thirds of the octahedral interstices (Fig. 1). A given metal ion, $M(1)$, has four near-metal neigh-

TABLE II
INTERATOMIC DISTANCES (Å) AND BOND ANGLES (DEGREES) FOR $(Ti_{1-x}V_x)_2O_3$ WITH STANDARD DEVIATIONS IN PARENTHESES

	$x=0^a$	0.005	0.01	0.02	0.04	0.07	0.10	0.30	0.50	0.70	0.90	1.00 ^b
M(1)-M(2)	2.578(2)	2.585(1)	2.595(1)	2.606(1)	2.627(1)	2.652(1)	2.659(1)	2.698(1)	2.708(1)	2.710(1)	2.713(1)	2.697(1)
M(1)-M(3)	2.994(1)	2.993(1)	2.990(1)	2.978(1)	2.970(1)	2.970(1)	2.967(1)	2.942(1)	2.921(1)	2.910(1)	2.910(1)	2.880(1)
M(1)-O(1)	2.066(1)	2.067(1)	2.069(2)	2.069(1)	2.070(1)	2.074(1)	2.072(1)	2.071(1)	2.066(1)	2.064(1)	2.059(1)	2.051(1)
M(1)-O(5)	2.027(1)	2.025(1)	2.023(1)	2.022(1)	2.017(1)	2.012(1)	2.012(1)	1.999(1)	1.988(1)	1.981(1)	1.977(1)	1.968(1)
O(1)-O(2)	2.796(1)	2.792(1)	2.792(3)	2.784(3)	2.772(2)	2.761(3)	2.752(1)	2.722(3)	2.703(3)	2.696(2)	2.683(2)	2.670(3)
O(1)-O(4)	2.791(1)	2.794(3)	2.794(3)	2.796(1)	2.799(1)	2.806(1)	2.806(1)	2.814(1)	2.813(1)	2.811(1)	2.807(1)	2.804(1)
O(1)-O(5)	2.880(1)	2.881(1)	2.884(1)	2.887(1)	2.890(1)	2.898(1)	2.900(4)	2.907(1)	2.904(1)	2.900(1)	2.899(1)	2.889(1)
O(4)-O(5)	3.073(2)	3.071(2)	3.068(2)	3.065(2)	3.057(1)	3.048(2)	3.047(1)	3.021(2)	2.998(2)	2.984(2)	2.977(2)	2.952(1)
O(1)-M(1)-O(2)	85.20(7)	85.05(5)	84.84(5)	84.57(5)	84.05(4)	83.48(5)	83.24(4)	82.16(5)	81.72(5)	81.55(5)	81.32(6)	81.45(7)
O(1)-M(1)-O(4)	85.96(2)	86.02(2)	86.13(2)	86.24(1)	86.44(1)	86.74(1)	86.80(5)	87.45(2)	87.84(2)	88.02(2)	88.10(2)	88.46(2)
O(1)-M(1)-O(5)	89.42(5)	89.50(4)	89.59(3)	89.76(4)	90.01(3)	90.32(4)	90.47(5)	91.14(4)	91.49(5)	91.60(4)	91.75(4)	91.90(5)
O(1)-M(1)-O(6)	170.01(8)	169.90(6)	169.78(7)	169.61(6)	169.26(5)	168.95(6)	168.78(10)	168.30(5)	168.20(4)	168.24(6)	168.10(7)	168.63(8)
O(4)-M(1)-O(5)	98.60(3)	98.61(3)	98.59(3)	98.56(2)	98.57(2)	98.48(5)	98.48(5)	98.16(2)	97.87(2)	97.74(2)	97.71(3)	97.17(3)
M(1)-O(1)-M(2)	77.18(9)	77.40(7)	77.67(7)	78.05(6)	78.75(6)	79.52(7)	79.84(1)	81.29(6)	81.88(7)	82.10(6)	82.41(7)	82.23(9)
M(1)-O(2)-M(3)	94.04(2)	93.98(2)	93.87(2)	93.76(1)	93.56(1)	93.26(2)	93.20(4)	92.55(2)	91.86(3)	91.98(2)	91.89(2)	91.54(3)
M(2)-O(2)-M(3)	132.33(5)	132.35(4)	132.37(4)	132.44(3)	132.52(3)	132.61(4)	132.69(6)	132.92(3)	133.04(4)	133.06(4)	133.14(4)	133.21(5)

^a Ref. (23).

^b Ref. (25).

TABLE III
VALUES OF 10 F_obs AND 10 F_calc.

Table with columns for h, k, l and rows for various values of V (0.5, 1.0, 2.0, 4.0, 7.0, 30.0, 50.0, 70.0, 90.0). Each row contains 10 columns of F_obs and 10 columns of F_calc values.

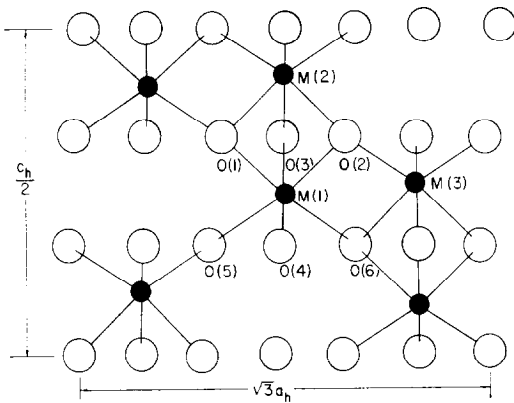


FIG. 1. A projection of the corundum structure on a plane perpendicular to the [110] axis.

bors; one sharing a triangular face of the coordination octahedron [$M(2)$ in Fig. 1] and three sharing edges of the octahedron [$M(3)$ in Fig. 1].

The values of the unit cell parameters in the Ti_2O_3 - V_2O_3 system at various compositions are shown in Table I and in Fig. 2. The

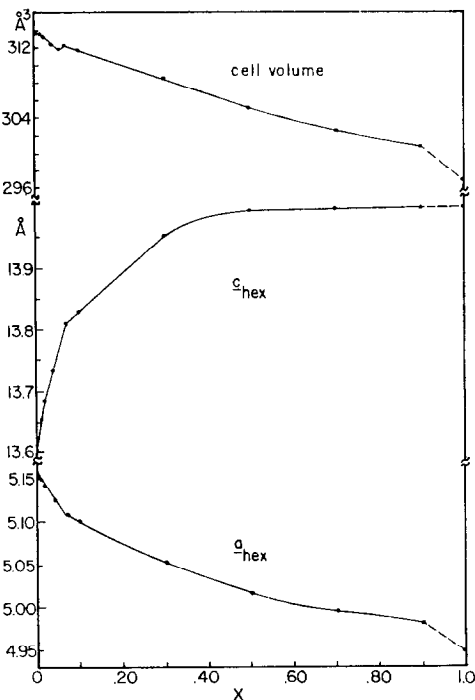


FIG. 2. Variation of unit cell parameters and cell volume in $(Ti_{1-x}V_x)_2O_3$.

data shown for Ti_2O_3 and V_2O_3 have been taken from Refs. (23, 26), respectively. Many unit cell determinations (33) and several refined crystal structures of Ti_2O_3 and V_2O_3 from single crystal data (22-27) are available. With the exception of the V_2O_3 parameters, all parameters reported were determined on the same instrument under the same conditions and thus comparisons of small changes should not be affected by possible systematic errors between equipment or by differences in conditions. The V_2O_3 distances and angles of Refs. (26, 27) are identical within 2 ESDs.

Adding V_2O_3 to Ti_2O_3 causes rapid changes in both axes in the low-vanadium region, with less pronounced changes at higher concentrations. Over half of the change in the c axis occurs between 0 and 7 at. % of V. Additionally, a plot of c axis length vs vanadium concentration is approximately linear from 0-2 and from 2-7% V, with a slight change in slope between these regions. There is a quite noticeable break in slope in the vicinity of 7% V. The c axis then increases more slowly, finally leveling off in the 50-100% V region. The a axis decreases abruptly between 0 and 7% V. Like the c axis, a varies linearly with composition from 0-2 and 2-7% V. A similar break in the slope of the a vs % V plot is seen around 7% V. Unlike c , the a axis does not level off but rather decreases throughout the entire composition range. A positive deviation from Vegard's law is observed for the a axis in the vicinity of 90% V. The behavior for $x = 0.9$ is consistent with that observed for $0.92 \leq x \leq 1.0$ (34).

As well as can be seen (only figures are presented), our cell constant data agree with the results of Kawabuko, Yanagi, and Nomura (21) and Loehman, Rao, and Honig (5). However, these earlier studies were carried out with rather limited data sets and so are not as precise and do not show as much detail as the present work. For example, our plot of cell volume vs concentration (Fig. 2) shows an unusual S-shaped wiggle between 0 and 10 at. % of V, a feature which had not been noticed before.

The c/a ratios of both Ti_2O_3 and V_2O_3 are unusual when compared to those of most corundum-like oxides (35). While α - Al_2O_3 ,

$\alpha\text{-Fe}_2\text{O}_3$, $\alpha\text{-Cr}_2\text{O}_3$, Rh_2O_3 , and Ga_2O_3 all have c/a ratios falling in the range 2.70–2.74, the Ti_2O_3 c/a ratio is abnormally small at 2.64; V_2O_3 shows the anomalously large value of 2.83. Rapid approaches toward more “normal” values of the c/a ratio are seen at both extreme ends of the composition scale (Table I).

The major change in the atomic coordinates of the $(\text{Ti}_{1-x}\text{V}_x)_2\text{O}_3$ system occurs in the metal z parameter. The z parameter for the metal atom at $(0,0,z)$ increases by some 57 ESDs (Table I). As with the c axis, over half of this change occurs in the 0–7 at. % of V region. z also shows linear increases from 0–2 and 2–7% V, followed by less rapid changes at higher vanadium concentrations. Unlike the c axis, which remains constant from 50 to 100% V, z decreases from $(\text{Ti}_{0.1}\text{V}_{0.9})_2\text{O}_3$ to pure V_2O_3 .

The oxygen x parameter changes no more than 5 to 7 ESDs throughout the entire composition range. Having virtually the same value in Ti_2O_3 and V_2O_3 x drops slightly in the alloys.

The thermal parameters are well behaved and have reasonable values for systems of this sort; however, they do not vary with composition in any coherent way. It should be mentioned that these crystals exhibit rather strong extinction, which has substantial effects on the temperature factor refinement (23). Extinction effects depend to some degree on crystal size. Thus, the use of crystals of different sizes causes enough scatter in the β_{ij} 's to obscure evidence of any subtle trends.

The changes in metal–metal distances caused by the changes in cell parameters and fractional atomic coordinates are shown in Table II and Fig. 3. The distance between metal ions sharing an octahedral face of their coordination polyhedra, $M(1)\text{--}M(2)$, increases sharply from 2.578(1) Å in Ti_2O_3 to 2.652(1) Å in $(\text{Ti}_{0.93}\text{V}_{0.07})_2\text{O}_3$, then more slowly to a maximum of 2.713(1) Å in $(\text{Ti}_{0.1}\text{V}_{0.9})_2\text{O}_3$, a total increase of 5.4% (the c axis increases by 2.9% over the same concentration range). The $M(1)\text{--}M(2)$ distance then decreases to 2.697(1) Å in V_2O_3 . The distance between edge-sharing metal neighbors, $M(1)\text{--}M(3)$, decreases continuously from 2.994(1) Å

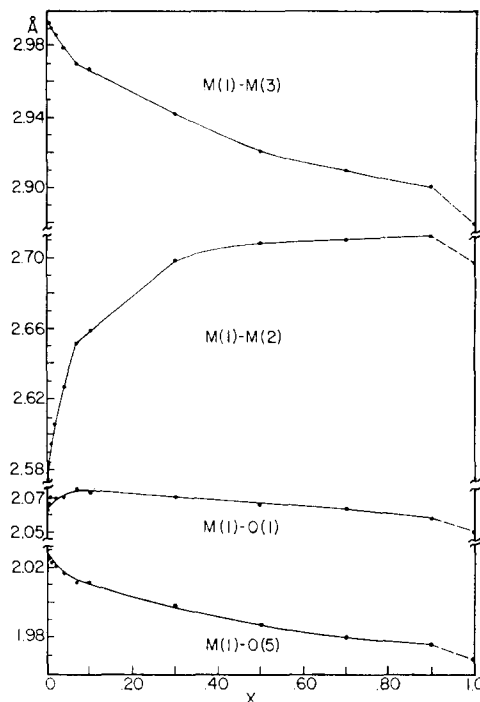


FIG. 3. Variation of metal–metal and metal–oxygen distances in $(\text{Ti}_{1-x}\text{V}_x)_2\text{O}_3$.

in Ti_2O_3 to 2.880(1) Å in V_2O_3 , a 3.8% change, while a decreases by 4.0%. Both the $M(1)\text{--}M(2)$ and $M(1)\text{--}M(3)$ distances depend linearly on composition from 0–2 and 2–7% V; plots of both distances vs. % V show distinct breaks in slope in the vicinity of 7 at. % V.

The effects of changing composition on the metal–oxygen and oxygen–oxygen distances are also shown in Table II and in Fig. 3. The 0–7% V concentration range will be discussed first. In these alloys, the distance from $M(1)$ to an oxygen in the shared octahedral face, $M(1)\text{--}O(1)$, increases from 2.062(1) Å in Ti_2O_3 to 2.074(1) Å in $(\text{Ti}_{0.93}\text{V}_{0.07})_2\text{O}_3$. At the same time, the distance between oxygens in this shared face, $O(1)\text{--}O(2)$, decreases from 2.791(1) to 2.761(3) Å. Thus as $M(1)$ and $M(2)$ move apart, their shared oxygens move closer together. The distance from $M(1)$ to an oxygen in the opposite octahedral face, $M(1)\text{--}O(5)$, decreases from 2.028(1) Å in Ti_2O_3 to 2.012(1) Å in $(\text{Ti}_{0.93}\text{V}_{0.07})_2\text{O}_3$ as

$M(1)$ approaches this face. The distance between oxygens in this unshared octahedral face, $O(4)$ – $O(5)$, also decreases with increasing vanadium content. Distances between oxygens in different closest packed layers, such as $O(1)$ – $O(4)$ and $O(1)$ – $O(5)$, show significant increases, as expected from the substantial increase in the c axis observed for this concentration range.

In the composition range from 7 to 90% vanadium, the $M(1)$ – $M(3)$ distance continues to decrease and $M(1)$ – $M(2)$ to increase, although in a more gradual manner than at lower vanadium concentrations. The metal–oxygen bonded distances decrease, reflecting the diminishing average size of the metal ion (36). Distances between oxygens in the same closest-packed layer, $O(1)$ – $O(2)$ and $O(4)$ – $O(5)$, continue to decrease, paralleling the a axis behavior. The interlayer oxygen–oxygen distances change little in this range.

Although no data other than cell dimensions (34) is yet available for samples in the concentration range 90–100% V_2O_3 , plainly there are structural changes here which are not continuations of the middle concentration range behavior. After essentially leveling off in the 50–90% V range, both $M(1)$ – $M(2)$ and $M(1)$ – $M(3)$ drop significantly from 90–100% V. The metal–oxygen distances decrease more steeply in this range than at lower vanadium concentrations. Among the oxygen–oxygen distances, $O(1)$ – $O(5)$ and $O(4)$ – $O(5)$ decrease rapidly between 90 and 100% V, but no unusual changes are seen in $O(1)$ – $O(4)$ or $O(1)$ – $O(2)$.

Discussion

The structural behavior observed in the Ti_2O_3 – V_2O_3 system as the composition changes cannot be explained by Vegard's law. The deviations from this law are especially striking in the low-vanadium alloys. In this composition range the interatomic distance changes are too great to be due to changes in ionic size; in fact, many of these distances change in the opposite direction to that expected from size considerations. Thus the structural changes caused by adding small

amounts of V_2O_3 to Ti_2O_3 must be due in large part to electronic effects related to the semiconductor–metal transition which occurs in lightly vanadium-doped Ti_2O_3 with increasing dopant concentration.

Ti_2O_3 is a semiconductor at room temperature, although a transition to metallic behavior occurs in the 150–350°C temperature range (2, 3). Adding increasing amounts of V_2O_3 to Ti_2O_3 successively lowers the room temperature resistivity of the alloy and decreases the magnitude of the resistivity drop across the semiconductor–metal transition without changing the transition temperature range (1). With the vanadium content somewhat greater than 2 at%, the alloy becomes metallic at all temperatures, though a small resistivity drop is still seen in the 150–350°C range. At about 7% V, this high-temperature transition disappears, and the room temperature resistivity becomes insensitive to vanadium content.

The greatest changes in all structural parameters in $(Ti_{1-x}V_x)_2O_3$ occur as x varies from 0 to 0.07. This is the composition range where electrical measurements show a decrease in resistivity and disappearance of the high-temperature resistivity anomaly. Several interatomic distances in these low-vanadium alloys change significantly with doping. However, as with the structural changes observed in Ti_2O_3 upon heating (22, 23), these structural changes can be described satisfactorily as the result of an increase in the $M(1)$ – $M(2)$ distance coupled with reorganization of the structure in order to minimize changes in metal–oxygen distances. As $M(1)$ and $M(2)$ move apart, their shared oxygens move together to counteract the lengthening of the $M(1)$ – $O(1)$ distance, and the oxide layers move apart so that $M(1)$ – $O(5)$ remains reasonably constant. Thus the lengthening of the c axis with increasing vanadium content is caused by the increase in the $M(1)$ – $M(2)$ distance, while the contraction of the a axis reflects the inward motion of $O(1)$, $O(2)$, and $O(3)$ as they follow the metal motion. The decrease in the $M(1)$ – $M(3)$ distance is small, and can be ascribed to the movement of the shared oxygen toward $M(1)$, pulling $M(3)$ along with it. Thus we

see that large changes in the $M(1)$ – $M(2)$ distance at room temperature accompany the diminution and disappearance of the resistivity drop which occurs between 150 and 350°C in lightly vanadium-doped Ti_2O_3 . Interestingly, the plots of many structural parameters vs % V also show a slight change in slope around 2 at % V, the composition corresponding to the onset of metallic behavior in the alloys.

The temperature-induced semiconductor–metal transition in pure Ti_2O_3 has been explained (13, 14, 37) in terms of a band-crossing model. In the proposed Ti_2O_3 band structure the valence band, a band of a_1 symmetry, is formed by the bonding interaction between d_{z^2} orbitals of c axis neighbor metal ions, $M(1)$ and $M(2)$. This band is completely filled at 0°K. At low temperatures, the valence band is separated by a small gap from the conduction band, of e symmetry, which is formed by overlapping d orbitals of edge-sharing metal neighbors in the basal plane, $M(1)$ and $M(3)$. As Ti_2O_3 is heated, electrons are thermally promoted across the gap from the a_1 to the e band. The resulting loss of electron density from the a_1 band causes a weakening and lengthening of the $M(1)$ – $M(2)$ bond. As this distance increases, the a_1 band is destabilized and so rises in energy until it crosses the e band, at which point Ti_2O_3 becomes metallic.

In vanadium-doped Ti_2O_3 , vanadium is known to act as an acceptor or p -type dopant (7). This behavior would also remove electrons from the valence band. Thus the same band shifts and atomic movements expected for pure Ti_2O_3 when it is heated should also occur with vanadium doping.

The increase observed in the $M(1)$ – $M(2)$ distance in $(\text{Ti}_{1-x}\text{V}_x)_2\text{O}_3$ as x increases from 0 to 0.07 is in agreement with structural predictions based on the band-crossing model. The changes in structural behavior which occur for $0 \leq x \leq 0.02$ can be understood if it is assumed that acceptor impurity levels introduced by V_2O_3 lie in the a_1 – e band gap of Ti_2O_3 . Thus as increasing vanadium content weakens the $M(1)$ – $M(2)$ bond and causes the a_1 band to rise in energy, the a_1 band crosses these impurity levels, resulting in

metallic behavior for $(\text{Ti}_{0.98}\text{V}_{0.02})_2\text{O}_3$. The existence of a narrow level within the a_1 band has been postulated by Van Zandt (20) to account for the anomalous low-temperature specific heat observed for vanadium concentrations of 2 at % V and greater. As the vanadium concentration increases to about 7%, the a_1 and e bands cross, and the high-temperature resistivity drop disappears. Thus the electrical transition observed at about 7% vanadium is analogous to the temperature-induced semiconductor–metal transition in pure Ti_2O_3 . Accordingly, the interatomic distances in $(\text{Ti}_{0.93}\text{V}_{0.07})_2\text{O}_3$ are almost identical to those in Ti_2O_3 at 350°C (22, 23), when allowance is made for the effects of ionic size and thermal expansion.

As the vanadium content in Ti_2O_3 – V_2O_3 alloys increases from 7 at % V, the $M(1)$ – $M(2)$ distance and the c axis increase more gradually than at lower concentrations, then level off at approximately 50% V. This behavior is consistent with a band model for V_2O_3 in which the e band is proposed to lie below the a_1 band in energy (38); this order is the reverse of that in Ti_2O_3 . Thus the a_1 band in Ti_2O_3 alloys is gradually destabilized with respect to the e band as the vanadium content increases, resulting in the observed increase in the $M(1)$ – $M(2)$ distance. The leveling off of $M(1)$ – $M(2)$ at 50% V could result if the a_1 band in this alloy has risen in energy enough to be essentially unpopulated, so that further energy shifts cause negligible changes in bond order.

Apart from the c axis and $M(1)$ – $M(2)$ distance behavior, the structural changes in $(\text{Ti}_{1-x}\text{V}_x)_2\text{O}_3$, $0.07 \leq x \leq 0.90$, can be explained rather well by the effects of changing effective ionic size. However, our limited data suggest that some unusual structural behavior occurs in the 90–100% V range. It has been observed that adding small amounts of Ti_2O_3 to V_2O_3 has drastic effects on the insulator–metal transition which occurs in pure V_2O_3 at 150°K (39). Though the effect of Ti doping on the room temperature resistivity of these alloys is rather minor, evidently some structural changes do result. Interpretation of these changes awaits more detailed structural study of this composition region (40).

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